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STUDYING OF PHOTOSENSITIVITY AND GAS SENSITIVITY OF Si-CdTe-ZnO HETEROSTRUCTURES

The studying of the photocurrent relaxation kinetics in Si-CdTe-ZnO semiconductor heterostructure at illumination of light of 632 and 458 nm wave lengths and influence of light on sensitivity to ethyl alcohol vapor was carried. It was shown, that photocurrent relaxation kinetics is qualitatively dependent on the wave length of illuminating light, and the light causes growth of adsorptive response.

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